

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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HAT2140H

Silicon N Channel Power MOS FET
Power Switching

RENESAS

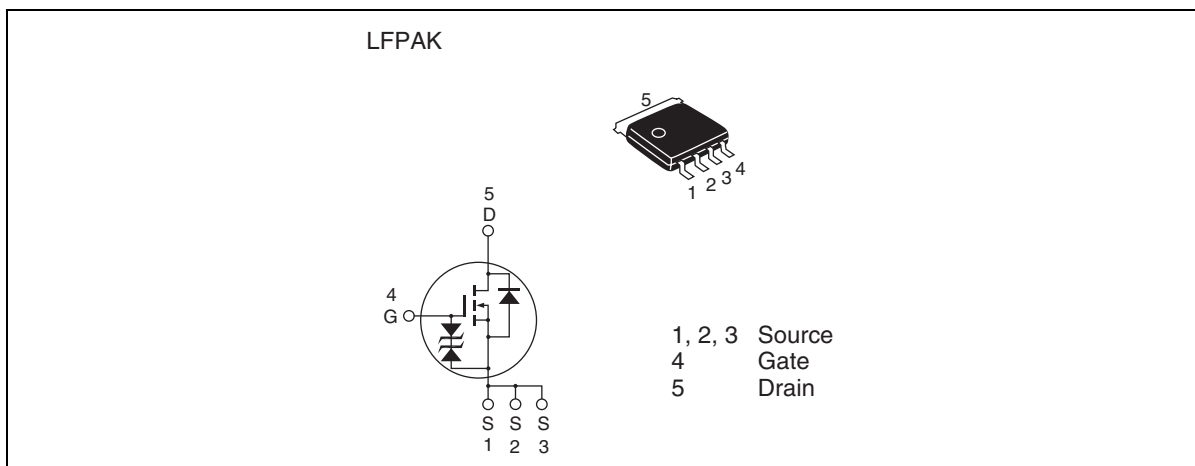
ADE-208-1581B(Z)

Preliminary
3rd. Edition
Aug. 2002

Features

- Capable of 7 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
 $R_{DS(on)} = 12.5 \text{ m}\Omega$ typ. (at $V_{GS} = 10 \text{ V}$)

Outline



HAT2140H

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	100	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	25	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	100	A
Body-drain diode reverse drain current	I_{DR}	25	A
Avalanche current	I_{AP} ^{Note 3}	25	A
Avalanche energy	E_{AR} ^{Note 3}	62.5	mJ
Channel dissipation	P_{ch} ^{Note2}	30	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to + 150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. $T_c=25^\circ C$
3. Value at Tch = 25°C, $R_g \geq 50 \Omega$

Electrical Characteristics

(Ta = 25°C)

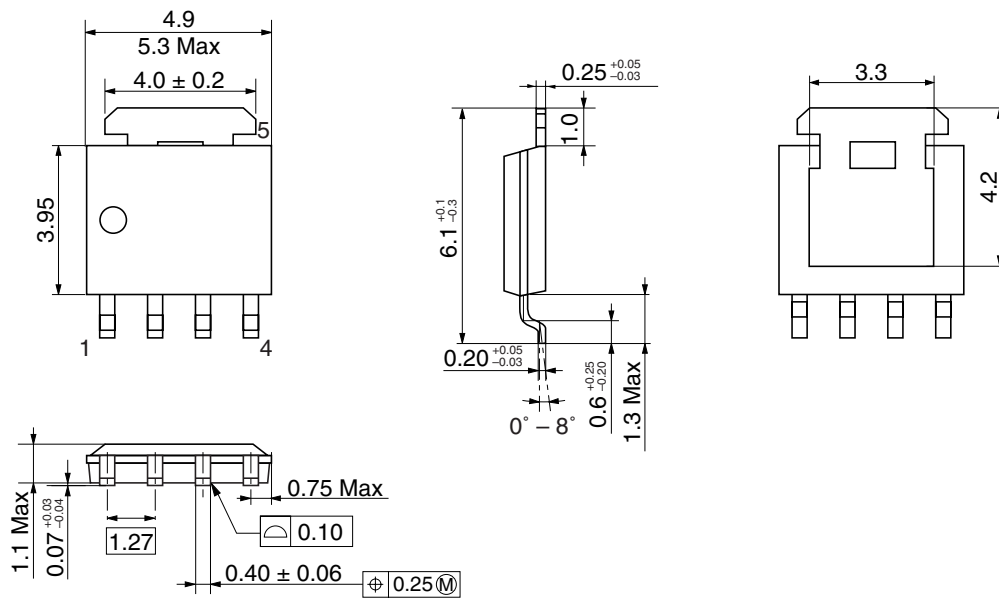
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 100 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	12.5	16.0	$\text{m}\Omega$	$I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	13.5	18.0	$\text{m}\Omega$	$I_D = 12.5 \text{ A}, V_{GS} = 7 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	27	45	—	S	$I_D = 12.5 \text{ A}, V_{DS} = 10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	6500	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	480	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	210	—	pF	$f = 1 \text{ MHz}$
Total gate charge	Q_g	—	105	—	nc	$V_{DD} = 50 \text{ V}$
Gate to source charge	Q_{gs}	—	20	—	nc	$V_{GS} = 10 \text{ V}$
Gate to drain charge	Q_{gd}	—	22	—	nc	$I_D = 25 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	25	—	ns	$V_{GS} = 10 \text{ V}, I_D = 12.5 \text{ A}$
Rise time	t_r	—	24	—	ns	$V_{DD} \cong 30 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	100	—	ns	$R_L = 2.4 \text{ }\Omega$
Fall time	t_f	—	12	—	ns	$R_g = 4.7 \text{ }\Omega$
Body-drain diode forward voltage	V_{DF}	—	0.83	1.08	V	$I_F = 25 \text{ A}, V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	55	—	ns	$I_F = 25 \text{ A}, V_{GS} = 0$ $diF/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

HAT2140H

Package Dimensions

As of January, 2002
Unit: mm



Hitachi Code	LFPK
JEDEC	—
JEITA	—
Mass (reference value)	0.080 g

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